

Product Overview

NGTB25N120FL: IGBT, 1200 V, 25 A, FS1 Solar/UPS

For complete documentation, see the data sheet.



This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for UPS and solar applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Low Saturation Voltage using Trench with Field Stop Technology
- Low Switching Loss
- 10 μ s Short Circuit Capability
- Soft, Fast Free Wheeling Diode

Applications

- Power Conversion

Benefits

- Reduces System Power Dissipation
- Robust Circuit Performance

End Products

- UPS System
- Solar Inverter

For more information please contact your local sales support at www.onsemi.com.

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